Preferred Device

## **Triacs**

## **Silicon Bidirectional Thyristors**

Designed primarily for full-wave ac control applications, such as lighting systems, heater controls, motor controls and power supplies; or wherever full-wave silicon-gate-controlled devices are needed.

- Off-State Voltages to 800 Volts
- All Diffused and Glass Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Thermal Resistance and High Heat Dissipation
- Gate Triggering Guaranteed in Four Modes
- **%** Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MAC223A6FP, Date Code

## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)  MAC223A6FP MAC223A8FP	V <sub>DRM</sub> , V <sub>RRM</sub>	400 600	Volts
MAC223A10FP  On-State RMS Current $(T_C = +80^{\circ}C)^{(2)}$	I <sub>T(RMS)</sub>	800 25	Amps
Full Cycle Sine Wave 50 to 60 Hz		,C	
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = 80°C) Preceded and followed by rated current	I <sub>TSM</sub>	250	Amps
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	260	A <sup>2</sup> s
Peak Gate Power (t $\leq$ 2 µsec; T <sub>C</sub> = +80°C)	Р <sub>GМ</sub>	20	Watts
Average Gate Power (t = 8.3 ms; T <sub>C</sub> = +80°C)	P <sub>G(AV)</sub>	0.5	Watt
Peak Gate Current (t ≤ 2 µsec; T <sub>C</sub> = +80°C)	I <sub>GM</sub>	2.0	Amps
Peak Gate Voltage (t ≤ 2 μsec; T <sub>C</sub> = +80°C)	V <sub>GM</sub>	±10	Volts
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity ≤ 20%) (%)	V <sub>(ISO)</sub>	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C
Mounting Torque	_	8.0	in. lb.

- (1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) The case temperature reference point for all  $T_{\rm C}$  measurements is a point on the center lead of the package as close as possible to the plastic body.



#### ON Semiconductor

http://onsemi.com

## ISOLATED TRIAC (%) 25 AMPERES RMS 400 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 3

PIN ASSIGNMENT		
1	Main Terminal 1	
2	Main Terminal 2	
3	Gate	

#### **ORDERING INFORMATION**

Device	Package	Shipping
MAC223A6FP	ISOLATED TO220FP	500/Box
MAC223A8FP	ISOLATED TO220FP	500/Box
MAC223A10FP	ISOLATED TO220FP	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

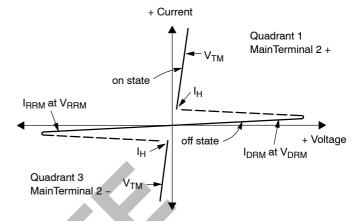
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T <sub>L</sub>	260	°C

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

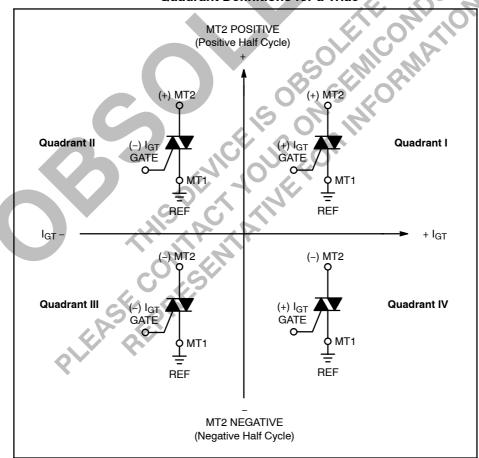
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•					
· · · · · · · · · · · · · · · · · · ·	25°C 125°C	I <sub>DRM</sub> , I <sub>RRM</sub>	_ _	_	10 2.0	μA mA
ON CHARACTERISTICS						
Peak On-State Voltage $(I_{TM} = \pm 35 \text{ A Peak, Pulse Width} \le 2 \text{ ms; Duty Cycle} \le 2\%)$		V <sub>TM</sub>	_	1.4	1,85	Volts
Gate Trigger Current (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) \\ MT2(+),\ G(+);\ MT2(-),\ G(-);\ MT2(+),\ G(-) \\ MT2(-),\ G(+) $		I <sub>GT</sub>		20 30	50 75	mA
Gate Trigger Voltage (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) \\ MT2(+),\ G(+);\ MT2(-),\ G(-);\ MT2(+),\ G(-) \\ MT2(-),\ G(+) $		V <sub>GT</sub>		1.1 1.3	2.0 2.5	Volts
Gate Non-trigger Voltage $(V_D = 12 \text{ V}, T_J = 125^{\circ}\text{C}, R_L = 100 \Omega)$ All Quadrants	S	V <sub>GD</sub>	0.2	0.4	-	Volts
Holding Current ( $V_D = 12 \text{ Vdc}$ , Gate Open, Initiating Current = $\pm 200 \text{ mA}$ )		正		10	50	mA
Gate Controlled Turn-On Time (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 35 A Peak, I <sub>G</sub> = 200 mA)	0	t <sub>gt</sub>	_	1.5	_	μs
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, T_C = 125°C)$		dv/dt	_	40	_	V/μs
Critical Rate of Rise of Commutation Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 35 A Peak, Commutating di/dt = 12.6 A/ms, Gate Unenergized, T <sub>C</sub> = 80°C)		dv/dt(c)	_	5.0		V/µs
didit = 12.07 (iiio, date offorforgized, 10 = 60 of						

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



## **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

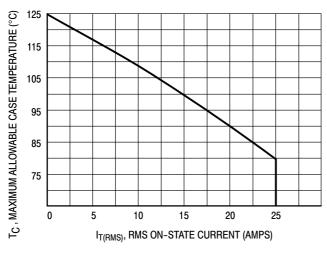


Figure 1. RMS Current Derating

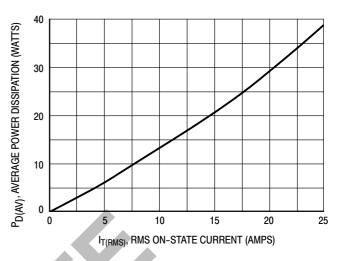
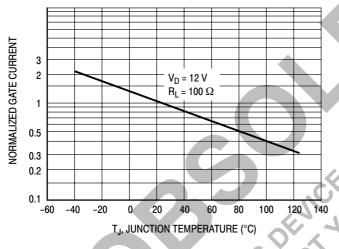


Figure 2. On-State Power Dissipation



**Figure 3. Typical Gate Trigger Current** 

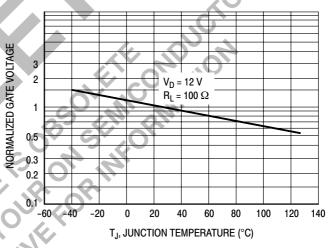


Figure 4. Typical Gate Trigger Voltage

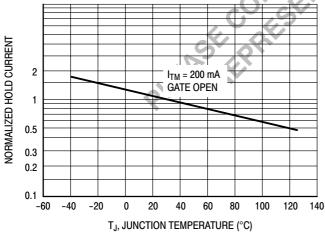


Figure 5. Typical Hold Current

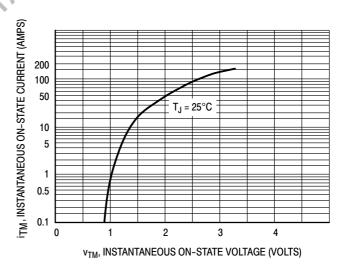
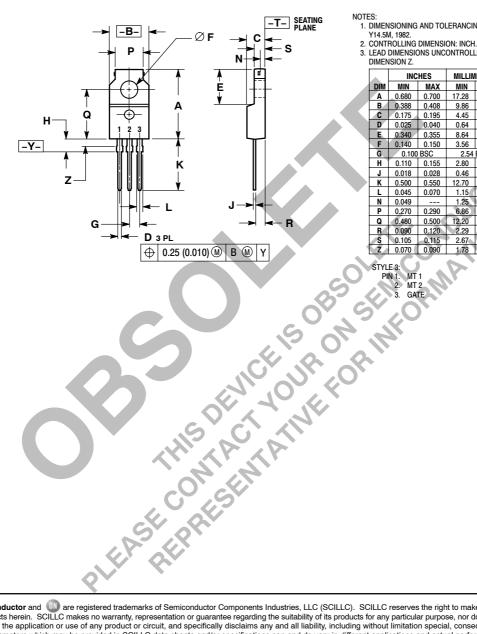


Figure 6. Typical On-State Characteristics

#### PACKAGE DIMENSIONS

#### ISOLATED TO-220 Full Pack

CASE 221C-02 **ISSUE C** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

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